

FEATURES

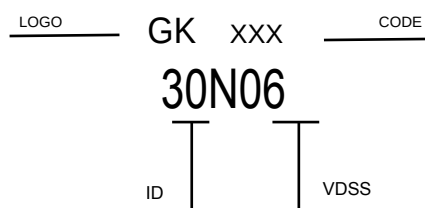
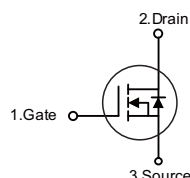
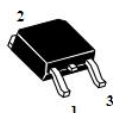
100% EAS Guaranteed
Green Device Available
Super Low Gate Charge
Excellent CdV/dt effect decline
Advanced high cell density Trench technology

DESCRIPTION

The 30N06 is the high cell density trenchd N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The 30N06 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

V_{DSS} 60 V
 I_D 30 A
 $R_{DS(ON)}$ 23 m Ω



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		60	V
V_{GSS}	Gate-Source Voltage		± 30	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	30	A
		$T_C = 100^\circ\text{C}$	13	A
I_{DM}	Pulsed Drain Current ^{note1}		100	A
EAS	Single Pulsed Avalanche Energy ^{note2}		39	mJ
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	41.7	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		50	$^\circ\text{C/W}$
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +175	$^\circ\text{C}$

Electrical characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics							
Drain-Source Breakdown Voltage		V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	60	-	-	V
Gate-Body Leakage Current		I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
Zero Gate Voltage Drain Current	T _J =25°C	I _{DSS}	V _{DS} = 60V, V _{GS} = 0V	-	-	1	μA
	T _J =100°C			-	-	100	
Gate-Threshold Voltage		V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.2	1.7	2.5	V
Drain-Source on-Resistance ⁴		R _{DS(on)}	V _{GS} = 10V, I _D = 10A	-	23	32	mΩ
			V _{GS} = 4.5V, I _D = 5A	-	31.5	40	
Forward Transconductance ⁴		g _{fs}	V _{DS} = 5V, I _D = 10A	-	15.5	-	S
Dynamic Characteristics ⁵							
Input Capacitance		C _{iss}	V _{DS} = 30V, V _{GS} =0V, f =1MHz	-	1355	-	pF
Output Capacitance		C _{oss}		-	60	-	
Reverse Transfer Capacitance		C _{rss}		-	49	-	
Gate Resistance		R _G	f =1MHz	-	1.2	-	Ω
Switching Characteristics ⁵							
Total Gate Charge		Q _g	V _{GS} = 10V, V _{DD} = 30V, I _D = 10A	-	22	-	nC
Gate-Source Charge		Q _{gs}		-	4.2	-	
Gate-Drain Charge		Q _{gd}		-	6.9	-	
Turn-on Delay Time		t _{d(on)}	V _{GS} =10V, V _{DD} = 30V, R _G = 3Ω, I _D = 10A	-	6.4	-	ns
Rise Time		t _r		-	15.3	-	
Turn-off Delay Time		t _{d(off)}		-	25	-	
Fall Time		t _f		-	7.6	-	
Body Diode Reverse Recovery Time		t _{rr}	I _F =10A, dI _F /dt=100A/μs	-	26	-	ns
Body Diode Reverse Recovery Charge		Q _{rr}		-	45	-	nC
Drain-Source Body Diode Characteristics							
Diode Forward Voltage ⁴		V _{SD}	I _S = 10A, V _{GS} = 0V	-	-	1.2	V
Continuous Source Current	T _C =25°C	I _S	-	-	-	30	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^\circ\text{C}$
2. The EAS data shows Max. rating . The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.4mH, I_{AS}=14A$
3. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
5. This value is guaranteed by design hence it is not included in the production test.

RATING AND CHARACTERISTIC CURVES

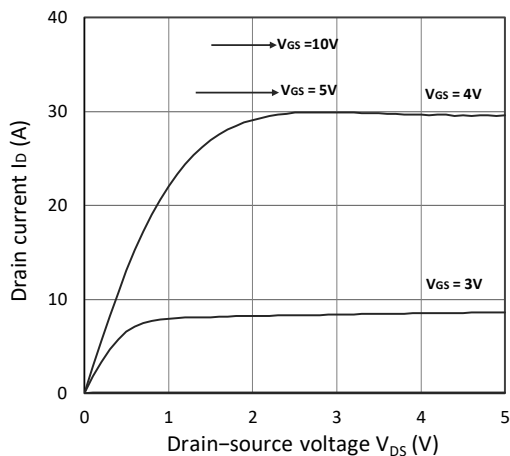


Figure 1. Output Characteristics

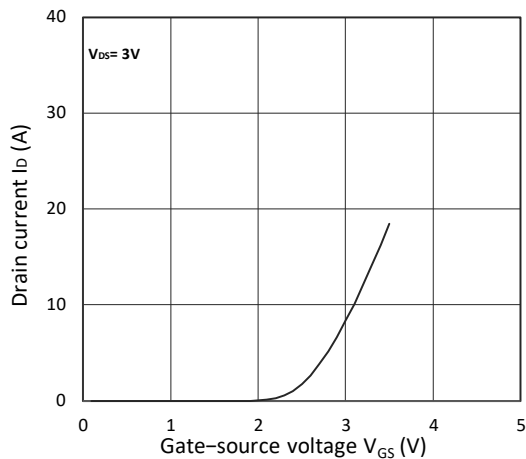


Figure 2. Transfer Characteristics

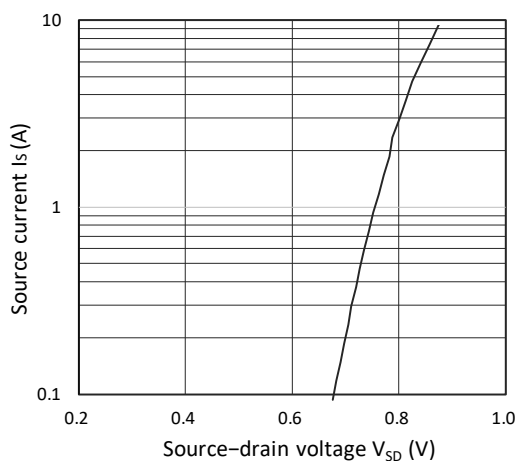


Figure 3. Forward Characteristics of Reverse

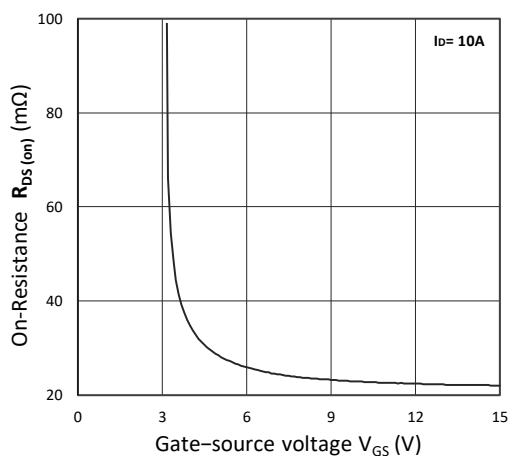


Figure 4. $R_{DS(on)}$ vs. V_{GS}

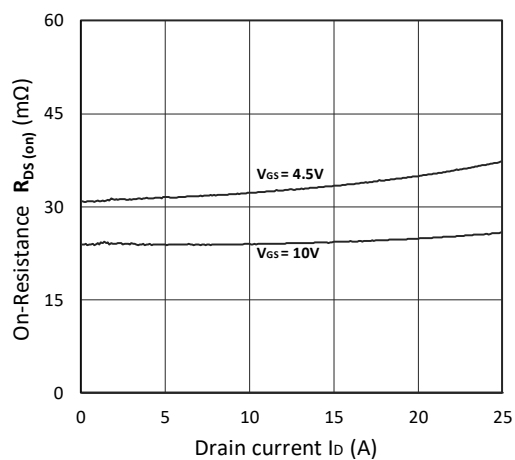


Figure 5. $R_{DS(on)}$ vs. I_D

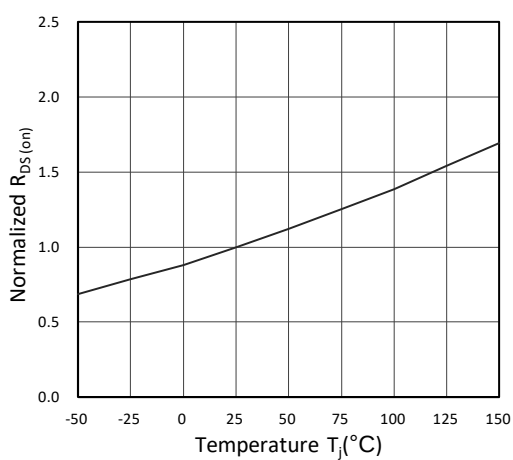


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

RATING AND CHARACTERISTIC CURVES

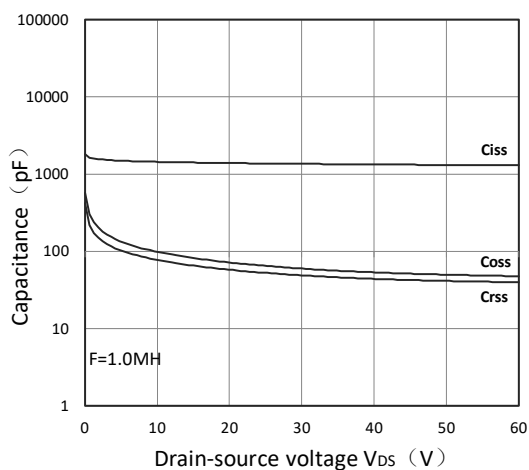


Figure 7. Capacitance Characteristics

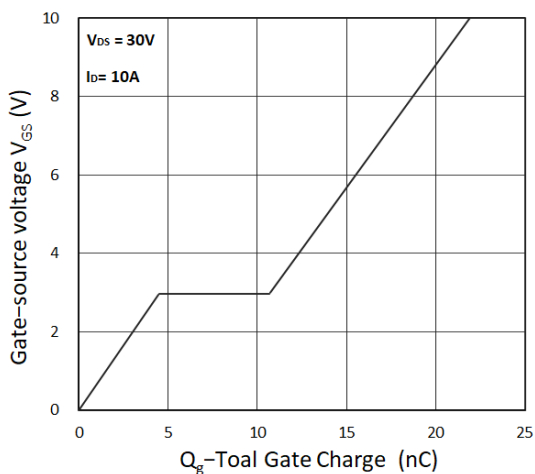


Figure 8. Gate Charge Characteristics

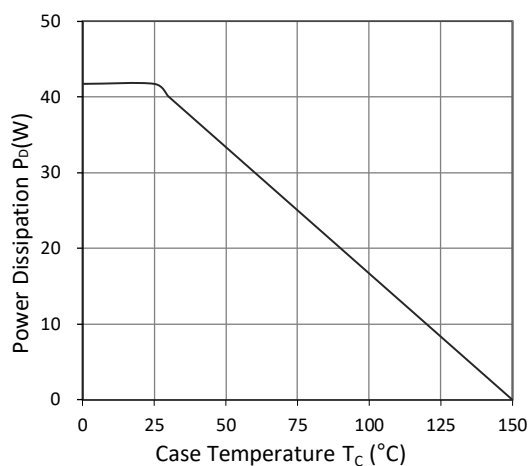


Figure 9. Power Dissipation

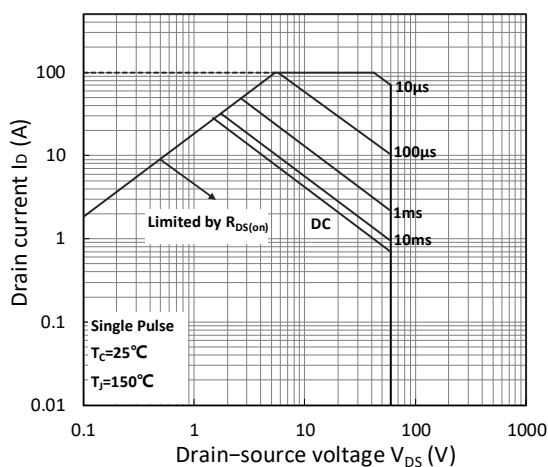


Figure 10. Safe Operating Area

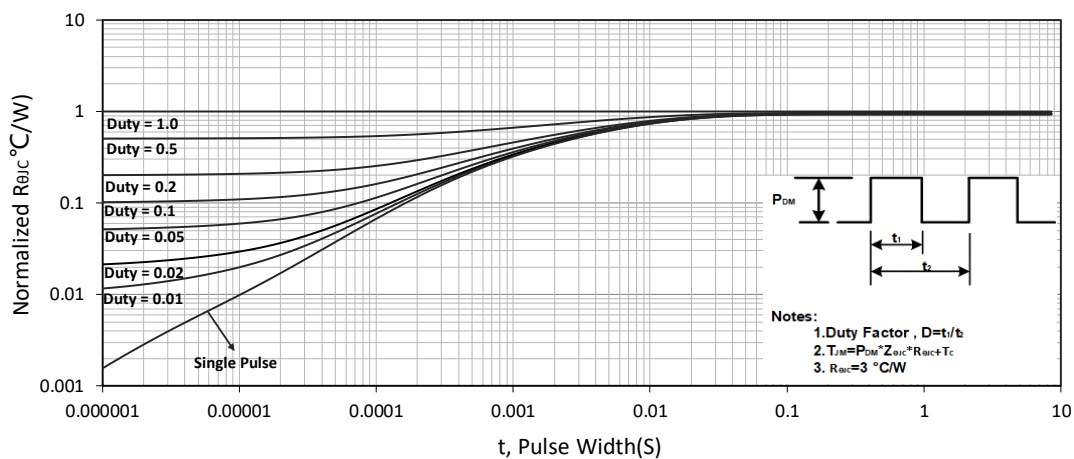
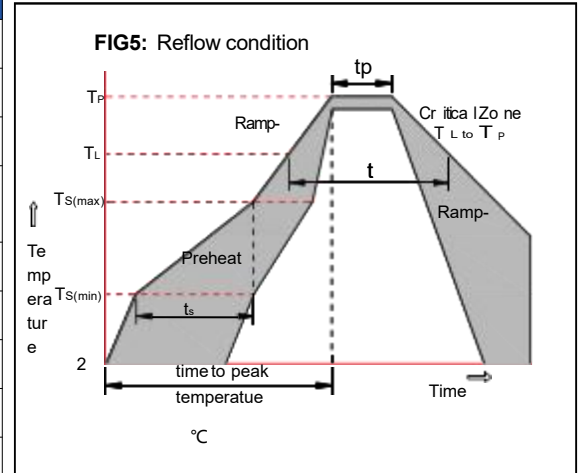


Figure 11. Normalized Maximum Transient Thermal Impedance

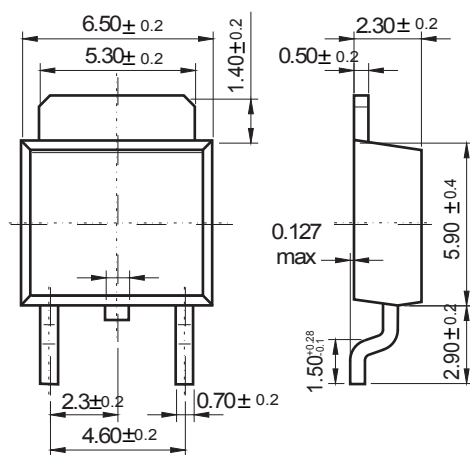
Soldering parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150 °C
	-Temperature Max ($T_{s(max)}$)	+200 °C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3 °C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3 °C/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217 °C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5) °C
Time within 5 °C of actual Peak Temp (t_P)		30 secs. Max
Ramp-down Rate		6 °C/sec. Max
Time 25 °C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260 °C

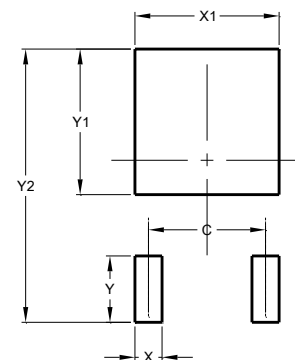


Package Dimensions & Suggested Pad Layout

TO-252

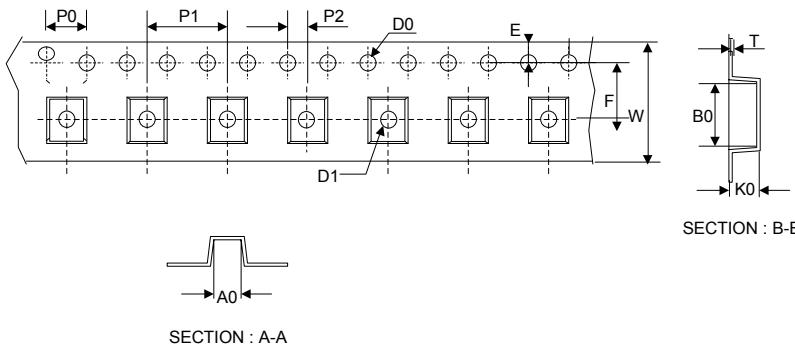
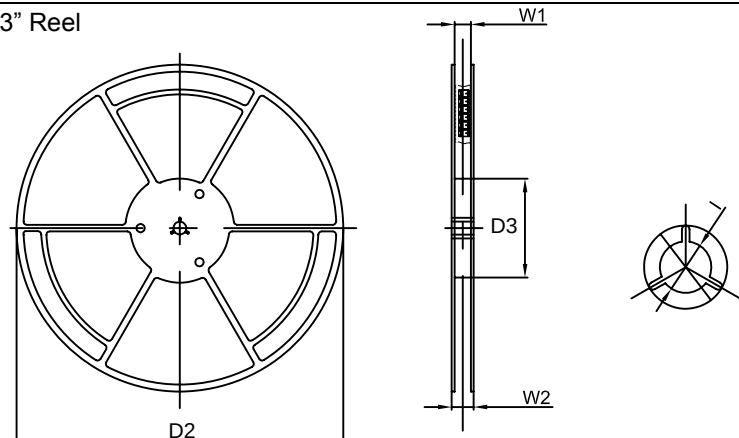


Dimensions in inches and (millimeters)



Dimensions	Value (in mm)
C	4.55
X	1.50
X1	5.80
Y	2.70
Y1	6.00
Y2	10.90

Tape & reel specification

Tape		Symbol	Dimension (mm)
 SECTION : A-A SECTION : B-B		P0	4.00±0.20
		P1	8.00±0.20
		P2	2.00±0.20
		D0	1.55±0.15
		D1	1.55±0.20
		E	1.75±0.20
		F	7.50±0.20
		W	16.00±0.20
		A0	7.10±0.20
		B0	10.50±0.20
		K0	2.70±0.20
		T	0.30±0.10
		D2	330.0±5.0
		D3	100.0±4.0
		W1	20.0±5.0
13" Reel		W2	I
		D2	13.0±2.0
		Quantity: 2500PCS	